

#### 30V N-Channel Enhancement Mode MOSFET – ESD Protected

Voltage 30 V Current 1.6A

#### **Features**

- RDS(ON), VGS@4,5V, ID@1.6A<200mΩ
- RDS(ON), VGS@2.5V, ID@1.1A<270mΩ</li>
- RDS(ON), VGS@1.8V, ID@0.2A<570mΩ
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

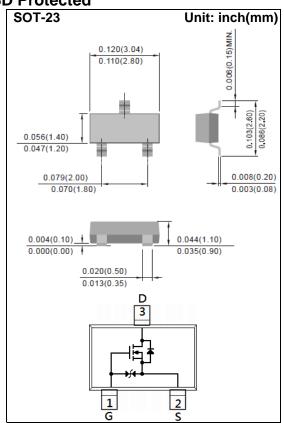
#### **Mechanical Data**

• Case: SOT-23 Package

Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0003 ounces, 0.0084 grams

Marking: A32



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 8	V
Continuous Drain Current		I <sub>D</sub>	1.6	Α
Pulsed Drain Current <sup>(Note 4)</sup>		I <sub>DM</sub>	6.4	А
Power Dissipation	T <sub>a</sub> =25°C	_	1.25	W
	Derate above 25°C	P <sub>D</sub>	10	mW/°C
Operating Junction and Storage Temperature Range		TJ,TSTG	-55~150	°C
Typical Thermal Resistance				
- Junction to Ambient <sup>(Note 3)</sup>		$R_{\theta JA}$	100	°C/W



### **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.5	0.78	1.3	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.6A	-	145	200	mΩ	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1.1A	-	185	270		
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =0.2A	-	330	570		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	0.01	1	uA	
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V	-	1.4	<u>+</u> 10	uA	
Dynamic <sup>(Note 5)</sup>							
Total Gate Charge	$Q_g$	\/ A5\/   A 6\	-	1.5	-	nC	
Gate-Source Charge	$Q_gs$	V <sub>DS</sub> =15V, I <sub>D</sub> =1.6A,	-	0.3	-		
Gate-Drain Charge	$Q_gd$	VGS=4.5V(1000 1,2)	-	0.3	-		
Input Capacitance	Ciss	\	-	93	-	pF	
Output Capacitance	Coss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V,	-	19	-		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	6	-		
Turn-On Delay Time	td <sub>(on)</sub>	\/ 45\/ L 4.0A	-	6.4	-		
Turn-On Rise Time	tr	V <sub>DD</sub> =15V, I <sub>D</sub> =1.6A,	-	33	-		
Turn-Off Delay Time	td <sub>(off)</sub>	$V_{GS}=4.5V$ , $R_{G}=6\Omega^{(Note 1,2)}$	-	37	-	ns	
Turn-Off Fall Time	tf	KG=012(1000 1,2)	-	32	-		
Drain-Source Diode							
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	1.0	А	
Diode Forward Voltage	V <sub>SD</sub>	Is=1.0A, V <sub>GS</sub> =0V	-	0.81	1.2	V	

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.



#### **TYPICAL CHARACTERISTIC CURVES**

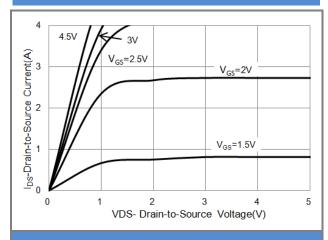
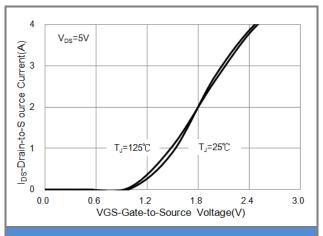


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

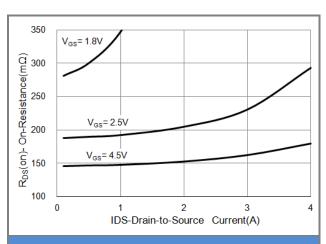


Fig.3 On-Resistance vs. Drain Current

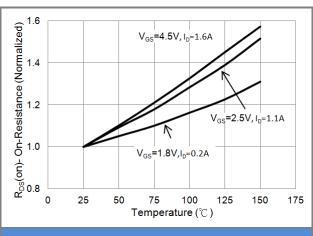
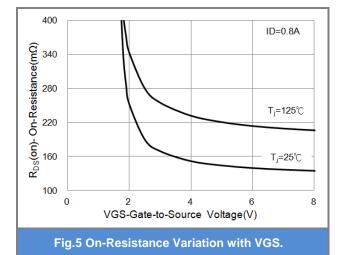
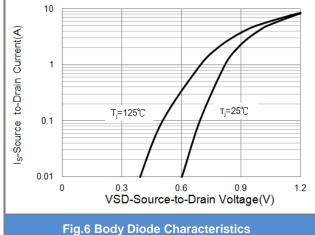


Fig.4 On-Resistance vs. Junction temperature







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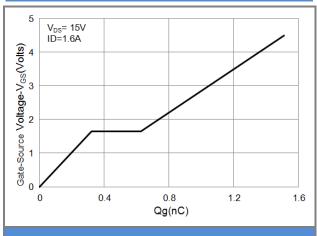


Fig.7 Gate-Charge Characteristics

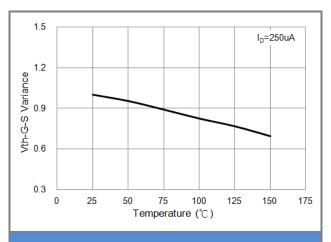


Fig.8 Threshold Voltage Variation with Temperature.

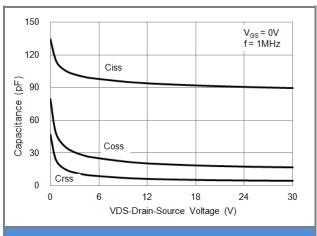


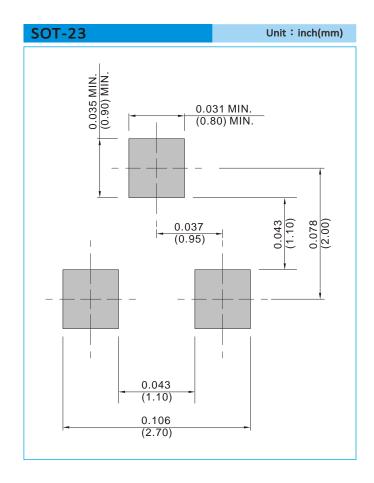
Fig.9 Capacitance vs. Drain-Source Voltage.



# **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking
PJA3432	SOT-23	3K pcs / 7" reel	A32

### **Mounting Pad Layout**





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